

## ABSTRACT OF THE DISCLOSURE

A III group nitride system compound semiconductor light emitting element has a quantum well structure that includes a well layer of  $\text{Al}_{X1}\text{Ga}_{Y1}\text{In}_{1-X1-Y1}\text{N}$ , where  $0 < X1$ ,  $0 \leq Y1$  and  $X1+Y1 < 1$  and  
5 a barrier layer of  $\text{Al}_{X2}\text{Ga}_{Y2}\text{In}_{1-X2-Y2}\text{N}$ , where  $0 < X2$ ,  $0 \leq Y2$  and  $X2+Y2 < 1$ .  
The Al composition (X2) of barrier layer is equal to or smaller than that (X1) of well layer.